



# SiC - photodiode JEC 0,1SHT/ JEC 0,1SSHT



- characteristics :**
- ◆ spectral range 210 ... 380 nm
  - ◆ active arrea 0,055 mm<sup>2</sup>
  - ◆ high UV-responsivity 0,13 A/W
  - ◆ TO 18-package
  - ◆ suitable for operating temperatures up to 150 °C
  - ◆ components are in conformity with RoHS and WEEE

- applications :**
- ◆ UV-measurements only
  - ◆ UV-source control
  - ◆ flame detection

**maximum ratings:**

reverse voltage 20 V  
operating temperature range- 25 °C ... +150 °C  
storage temperature range -40 °C ... +150 °C  
soldering temperature (3s) 260 °C

**technical data :**

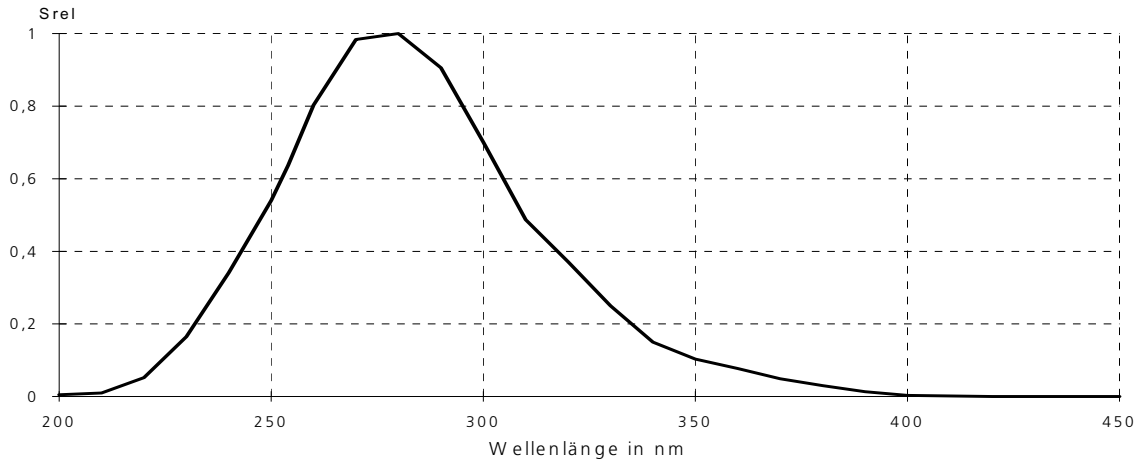
test conditions, as not otherwiese specified:  $\gamma_a = 25 \text{ °C}$ ,  $V_R = 0V$

parameter	test condition	min.	typ.	max.	unit
active area			0,25 x 0,25		mm <sup>2</sup>
spectral range		210		380	nm
maximumof spectral responsivity	$\lambda_{max} = 275 \text{ nm}$		0,13		A/W
absolute spectral responsivity	$\lambda = 254 \text{ nm}$		0,11		A/W
dark current $I_R$	$V_R = 1 \text{ V}$		1		fA
capacitance			21		pF

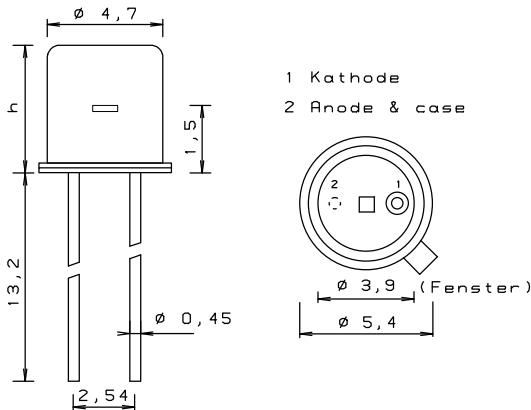
D  
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# JEC 0,1SHT/JEC 0,1SSHT

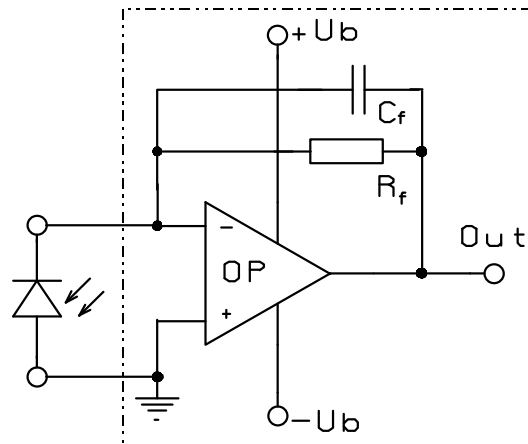
## relative spectral responsivity



## package dimensions



## application example



JEC 0,1SHT h = 5,2 mm  
 JEC 0,1SSHT h = 3,7 mm

The application example shows a typical circuit..  $R_f$  is responsible for the gain of the circuit.  $C_f$  compensates the reverse junction capacitance of the photodiode and input capacitance of the OPV. The exact value of  $C_f$  depends on  $R_f$ , used OPV and capacitance of the circuit. A typical value is 1 pF.

The diagram shows dependence of amplitude of the application circuit with OPA 111,  $R_f = 50 \text{ M}\Omega$  and  $C_f = 0.5 \text{ pF}$ .

